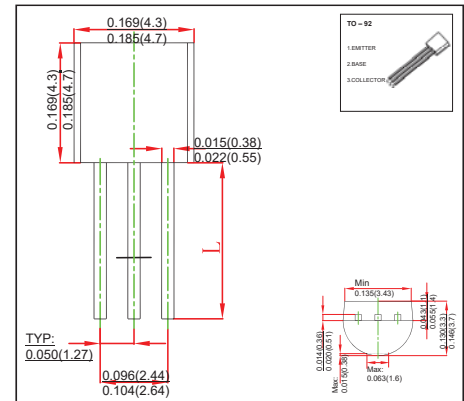


TO-92 Plastic-Encapsulate Transistors
FEATURES

- General Purpose Amplifier
- Low Noise UHF/VHF Amplifiers
- Low Frequency Drift, High Output UHF Oscillators
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	30	V
Collector-Emitter Voltage	VCEO	25	V
Emitter-Base Voltage	VEBO	3	V
Collector Current -Continuous	IC	40	mA
Collector Power Dissipation	PD	350	mW
Thermal Resistance from Junction to Ambient	R_{θ JA}	357	°C /W
Junction Temperature	T_j	1	°C
Storage Temperature	T_{stg}	-55~+150	°C

Electrical Specification (T_A=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =0.1mA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.01mA, I _C =0	3			V
Collector cut-off current	I _{CBO}	V _{CB} =25V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =2V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =10V, I _C =4mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =4mA, I _B =0.4mA			0.5	V
Base-emitter voltage	V _{BE}	I _C =4mA, V _{CE} =10V			0.95	V
Transition frequency	f _T	V _{CE} =10V, I _C =4mA, f=100MHz	650			MHz
Collector output capacitance	C _{cb}	V _{CB} =10V, I _E =0, f=1MHz			0.7	pF